

# Dual Series Switching Diode

## BAV99L, SBAV99L

### Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### MAXIMUM RATINGS (Each Diode)

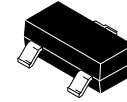
Rating	Symbol	Value	Unit
Reverse Voltage	$V_R$	100	Vdc
Forward Current	$I_F$	215	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	500	mAdc
Repetitive Peak Reverse Voltage	$V_{RRM}$	100	V
Average Rectified Forward Current (Note 1) (averaged over any 20 ms period)	$I_{F(AV)}$	715	mA
Repetitive Peak Forward Current	$I_{FRM}$	450	mA
Non-Repetitive Peak Forward Current $t = 1.0 \mu s$ $t = 1.0 ms$ $t = 1.0 s$	$I_{FSM}$	2.0 1.0 0.5	A

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

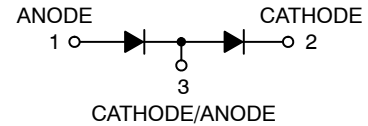
### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ C$ Derate above $25^\circ C$	$P_D$	225 1.8	mW mW/ $^\circ C$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ C/W$
Total Device Dissipation Alumina Substrate (Note 2) $T_A = 25^\circ C$ Derate above $25^\circ C$	$P_D$	300 2.4	mW mW/ $^\circ C$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ C/W$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-65 to +150	$^\circ C$

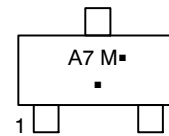
1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
2. Alumina =  $0.4 \times 0.3 \times 0.024$  in 99.5% alumina.



CASE 318  
SOT-23  
STYLE 11



### MARKING DIAGRAM



- A7 = Device Code
- M = Date Code\*
- = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
BAV99LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SBAV99LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
BAV99LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SBAV99LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# BAV99L, SBAV99L

## OFF CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted) (Each Diode)

Characteristic	Symbol	Min	Max	Unit
Reverse Breakdown Voltage, ( $I_{(BR)} = 100 \mu\text{A}$ )	$V_{(BR)}$	100	-	Vdc
Reverse Voltage Leakage Current, ( $V_R = 100 \text{ Vdc}$ ) ( $V_R = 25 \text{ Vdc}, T_J = 150^\circ\text{C}$ ) ( $V_R = 70 \text{ Vdc}, T_J = 150^\circ\text{C}$ )	$I_R$	-	1.0 30 50	$\mu\text{A}$ dc
Diode Capacitance, ( $V_R = 0, f = 1.0 \text{ MHz}$ )	$C_D$	-	1.5	pF
Forward Voltage, ( $I_F = 1.0 \text{ mAdc}$ ) ( $I_F = 10 \text{ mAdc}$ ) ( $I_F = 50 \text{ mAdc}$ ) ( $I_F = 150 \text{ mAdc}$ )	$V_F$	-	715 855 1000 1250	mVdc
Reverse Recovery Time, ( $I_F = I_R = 10 \text{ mAdc}, i_{R(REC)} = 1.0 \text{ mAdc}$ ) $R_L = 100 \Omega$	$t_{rr}$	-	6.0	ns
Forward Recovery Voltage, ( $I_F = 10 \text{ mA}, t_r = 20 \text{ ns}$ )	$V_{FR}$	-	1.75	V

## CURVES APPLICABLE TO EACH DIODE

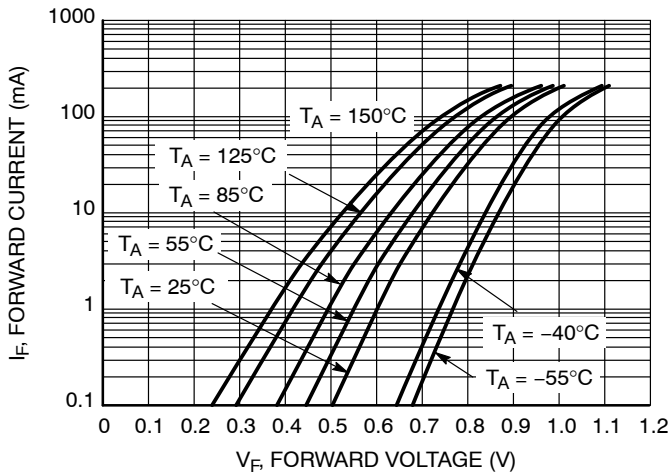


Figure 1. Forward Voltage

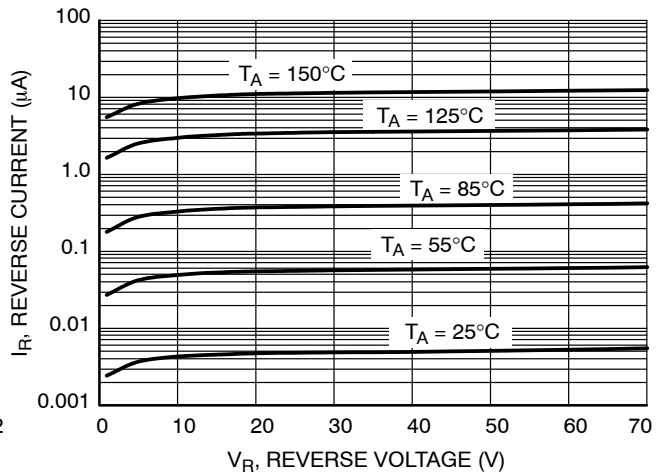


Figure 2. Leakage Current

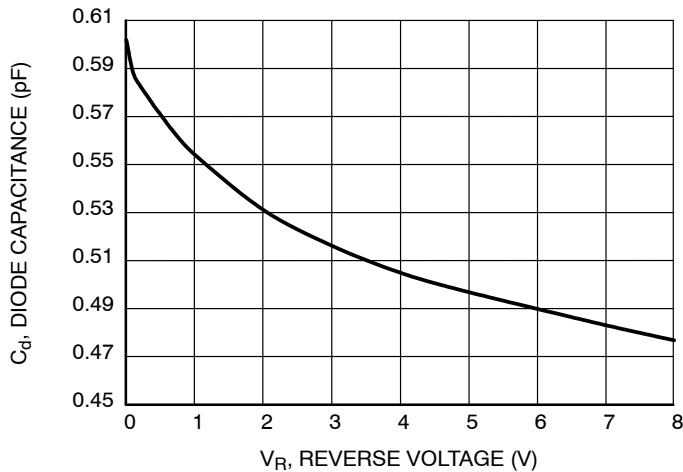


Figure 3. Capacitance

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



**SOT-23 (TO-236)**  
CASE 318  
ISSUE AT

DATE 01 MAR 2023

SCALE 4:1



**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
H <sub>E</sub>	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

**GENERIC MARKING DIAGRAM\***



- XXX = Specific Device Code
- M = Date Code
- = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



**RECOMMENDED MOUNTING FOOTPRINT**

\* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

**STYLES ON PAGE 2**

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# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS



### SOT-23 (TO-236) CASE 318 ISSUE AT

DATE 01 MAR 2023

STYLE 1 THRU 5:  
CANCELLED

STYLE 6:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

STYLE 7:  
PIN 1. EMITTER  
2. BASE  
3. COLLECTOR

STYLE 8:  
PIN 1. ANODE  
2. NO CONNECTION  
3. CATHODE

STYLE 9:  
PIN 1. ANODE  
2. ANODE  
3. CATHODE

STYLE 10:  
PIN 1. DRAIN  
2. SOURCE  
3. GATE

STYLE 11:  
PIN 1. ANODE  
2. CATHODE  
3. CATHODE-ANODE

STYLE 12:  
PIN 1. CATHODE  
2. CATHODE  
3. ANODE

STYLE 13:  
PIN 1. SOURCE  
2. DRAIN  
3. GATE

STYLE 14:  
PIN 1. CATHODE  
2. GATE  
3. ANODE

STYLE 15:  
PIN 1. GATE  
2. CATHODE  
3. ANODE

STYLE 16:  
PIN 1. ANODE  
2. CATHODE  
3. CATHODE

STYLE 17:  
PIN 1. NO CONNECTION  
2. ANODE  
3. CATHODE

STYLE 18:  
PIN 1. NO CONNECTION  
2. CATHODE  
3. ANODE

STYLE 19:  
PIN 1. CATHODE  
2. ANODE  
3. CATHODE-ANODE

STYLE 20:  
PIN 1. CATHODE  
2. ANODE  
3. GATE

STYLE 21:  
PIN 1. GATE  
2. SOURCE  
3. DRAIN

STYLE 22:  
PIN 1. RETURN  
2. OUTPUT  
3. INPUT

STYLE 23:  
PIN 1. ANODE  
2. ANODE  
3. CATHODE

STYLE 24:  
PIN 1. GATE  
2. DRAIN  
3. SOURCE

STYLE 25:  
PIN 1. ANODE  
2. CATHODE  
3. GATE

STYLE 26:  
PIN 1. CATHODE  
2. ANODE  
3. NO CONNECTION

STYLE 27:  
PIN 1. CATHODE  
2. CATHODE  
3. CATHODE

STYLE 28:  
PIN 1. ANODE  
2. ANODE  
3. ANODE

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